

The temperature dependence of the conductivity peak values in the single and the double quantum well nanostructures *n*-InGaAs/GaAs after IR-illumination

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The dependences of the longitudinal and Hall resistances on a magnetic field in *n*-InGaAs/GaAs heterostructures with a single and double quantum wells after infrared illumination are measured in the range of magnetic fields $B = 0-16$ T and temperatures $T = 0.05-4.2$ K.

Analysis of the experimental results was carried out on a base of two-parameter scaling hypothesis for the integer quantum Hall effect. The value of the second (irrelevant) critical exponent of the theory of two-parameter scaling was estimated.

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